# **BYC8-600**

# Hyperfast rectifier diode, low switching loss

Rev. 06 — 12 March 2009

**Product data sheet** 

# 1. Product profile

## 1.1 General description

Hyperfast rectifier diode in a SOD59 (2-lead TO-220AC) plastic package.

#### 1.2 Features and benefits

- Low reverse recovery current and low thermal resistance
- Reduces switching losses in associated MOSFET

## 1.3 Applications

- Continuous Current Mode (CCM)
   Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

#### 1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	600	V
I <sub>F(AV)</sub>	average forward current	square-wave pulse; $\delta$ = 0.5; $T_{mb} \le 109$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	8	Α
Dynamic	characteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V};$ $dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{\text{ A}}$	-	19	-	ns
Static ch	aracteristics					
V <sub>F</sub>	forward voltage	$I_F = 8 \text{ A}$ ; $T_j = 150 \text{ °C}$ ; see Figure 4	-	1.4	1.85	V



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# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	А	anode	mb	K — A 001aaa020
mb	mb	mounting base; cathode	SOD59 (TO-220AC)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC8-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
I <sub>F(AV)</sub>	average forward current	square-wave pulse; $\delta$ = 0.5; $T_{mb} \le 109$ °C; see Figure 1; see Figure 2	-	8	Α
I <sub>FRM</sub>	repetitive peak forward current	square-wave pulse; $\delta$ = 0.5; $t_p$ = 25 $\mu$ s; $T_{mb} \le 109$ °C	-	16	Α
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 150 °C	-	60	Α
	forward current	$t_p$ = 10 ms; sine-wave pulse; $T_{j(init)}$ = 150 °C	-	55	Α
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

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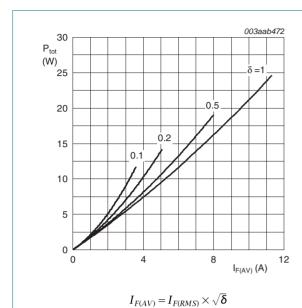


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

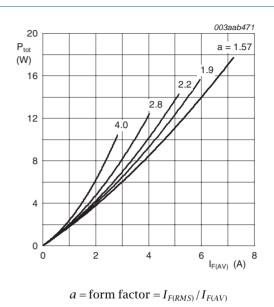


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 3	-	-	2.2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air		-	60	-	K/W

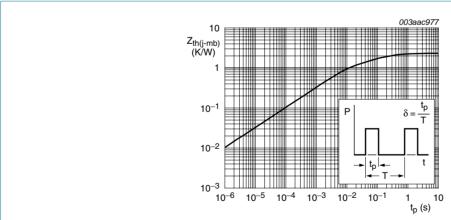


Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse width

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# 6. Characteristics

Table 6. Characteristics

Table 0.	Onaraotoriotico					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C	-	2	2.9	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; see <u>Figure 4</u>	-	1.4	1.85	V
		I <sub>F</sub> = 16 A; T <sub>j</sub> = 150 °C	-	1.7	2.3	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V	-	9	150	μΑ
		V <sub>R</sub> = 500 V; T <sub>j</sub> = 100 °C	-	1.1	3	mA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}t = 100 \text{ A/}\mu\text{s}; T_j = 25 \text{ °C}$	-	12	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}$	-	30	52	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}$	-	32	40	ns
		$I_F = 8 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $T_j = 25 ^{\circ}\text{C}$ ; see Figure 5	-	19	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}$	-	1.5	5.5	Α
		$I_F = 8 \text{ A}; \ V_R = 400 \text{ V}; \ dI_F/dt = 500 \text{ A/}\mu\text{s}; \ T_j = 100 \ ^{\circ}\text{C}$	-	9.5	12	Α
$V_{FR}$	forward recovery voltage	$I_F = 10 \text{ A}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; see Figure 6	-	8	10	V

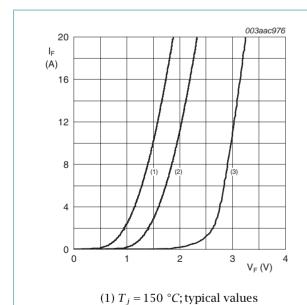


Fig 4. Forward current as a function of forward voltage

(2)  $T_j = 150 \, ^{\circ}C$ ; maximum values (3)  $T_j = 25 \, ^{\circ}C$ ; maximum values

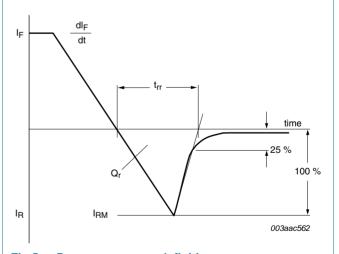
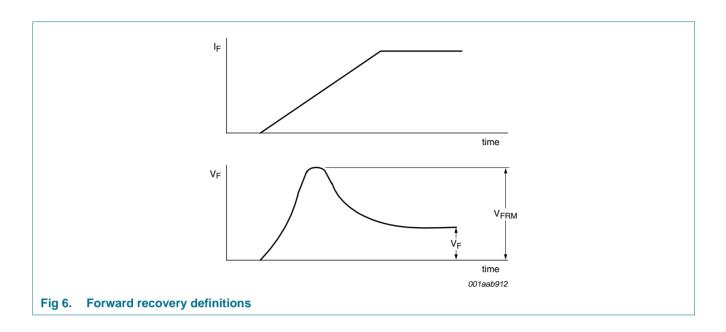


Fig 5. Reverse recovery definitions; ramp recovery

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# 7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC

SOD59

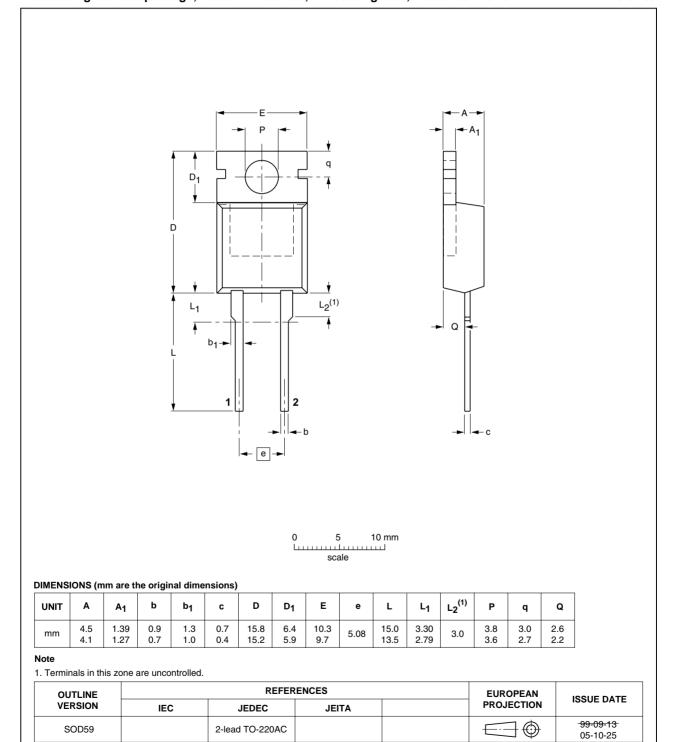


Fig 7. Package outline SOD59 (TO-220AC)

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# **Revision history**

#### Table 7. **Revision history**

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Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC8-600_6	20090312	Product data sheet	-	BYC8-600_5
Modifications:		at of this data sheet has be s of NXP Semiconductors.	en redesigned to comp	ly with the new identity
	<ul> <li>Legal text</li> </ul>	s have been adapted to th	e new company name v	where appropriate.
BYC8-600_5	20010401	Product specification	-	BYC8-600_4
BYC8-600_4	20001101	Product specification	-	BYC8-600_3
BYC8-600_3	19990501	Product specification	-	BYC8-600_2
BYC8-600_2	19980901	Product specification	-	BYC8-600_1
BYC8-600_1	19971001	Product specification	-	-

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#### 9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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